ESMT EMP8966

Fast Ultra High-PSRR, Low-Noise, Low-Dropout, 600mA Micropower CMOS Linear Regulator

General Description

The EMP8966 low-dropout (LDO) CMOS linear regulators, feature ultra-high power supply rejection ratio (75dB at 1kHz), low output voltage noise (30µV), low dropout voltage (270mV), low quiescent current (110µA), and fast transient response. It guarantees delivery of 600mA output current, and supports adjustable (1.2V to 5.0V) output voltage versions.

The EMP8966 is ideal for battery-powered applications by virtue of its low quiescent current consumption and its 1nA shutdown mode of logical operation. The regulator provides fast turn-on and start-up time by using dedicated circuitry to pre-charge an optional external bypass capacitor. This bypass capacitor is used to reduce the output voltage noise without adversely affecting the load transient response. The high power supply rejection ratio of the EMP8966 holds well for low input voltages typically encountered in battery- operated systems. The regulator is stable with small ceramic capacitive loads (2.2µF typical).

Additional features include regulation fault detection, bandgap voltage reference, constant current limiting and thermal overload protection. Available in miniature 5-pin SOT-23-5,SOT-23-6 package options are offered to provide additional flexibility for different applications.

EMP products is RoHS compliant.

Features

- Miniature SOT-23-5 and SOT-23-6 packages
- 600mA guaranteed output current
- 75dB typical PSRR at 1kHz
- 30µV RMS output voltage noise (10Hz to 100kHz)
- 270mV typical dropout at 600mA
- 110µA typical quiescent current
- 1nA typical shutdown mode
- Fast line and load transient response
- 80µs typical fast turn-on time
- 2.5V to 5.5V input range
- Stable with small ceramic output capacitors
- Over temperature and over current protection
- ±2% output voltage tolerance

Applications

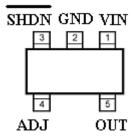
- Wireless handsets
- PCMCIA cards
- DSP core power
- Hand-held instruments
- Battery-powered systems
- Portable information appliances

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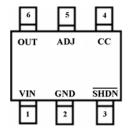


Connection Diagrams

SOT-23-5(Top View)



SOT-23-6(Top View)



Elite Semiconductor Memory Technology Inc.

Order information

EMP8966-XXVF05GRR/NRR

XXOperation Code VF05 SOT-23-5 Package GRR RoHS (Pb Free) Rating: -40 to 85°C

Package in Tape & Reel

NRR RoHS & Halogen free (By Request)

Rating: -40 to 85°C

Package in Tape & Reel

EMP8966-XXVC06GRR/NRR

XXOperation Code VC06 SOT-23-6 Package GRR RoHS (Pb Free)

Rating: -40 to 85°C

Package in Tape & Reel

NRR RoHS & Halogen free (By Request)

Rating: -40 to 85°C

Package in Tape & Reel



Order, Mark & Packing Information

No. of PIN	Adj	EN	СС	Package	Marking	Vout Code (XX)	Vout	Product ID
5	Y	Y	N	SOT-23-5	OUT ADJ 5 4 8966 Tracking Code PIN1 DOT 1 2 3 VIN GRND SHDN	00	Adj	EMP8966-00VF05GRR
6	Y	Y	Y	SOT-23-6	8966 Tracking Code PIN1 DOT PIN1 DOT AD STATE APP STATE APP	00	Adj	EMP8966-00VC06GRR

Old Marking: please see the notice (Page 18)

Package & Packing

SOT-23-5	3K units Tape & Reel
SOT-23-6	3K units Tape & Reel

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Typical Application

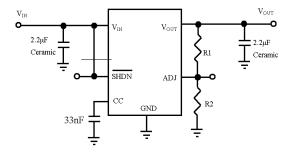


Fig. 1. EMP8966. Adjustable output version. Please refer to Application Information section for R1/R2 calculation.



Pin Functions

Name	SOT-23-5	SOT-23-6	Function
VOUT	5	6	Output Voltage Feedback.
VIN	1	1	Supply Voltage Input. Require a minimum input capacitor of close to $1\mu F$ to ensure stability and sufficient decoupling from the ground pin.
GND	2	2	Ground Pin.
ADJ	4	5	Adjustable Negative Feedback Control . Use external fixed resistors instead of trim pots to achieve the desired output voltage control.
сс		4	Compensation Capacitor. Connect an optimum 33nF noise bypass capacitor between the CC and the ground pins to reduce noise in VOUT.
SHDN	3	3	Shutdown Input. Set the regulator into the disable mode by pulling the SHDN pin low. To keep the regulator on during normal operation, connect the SHDN pin to VIN. The SHDN pin must not exceed VIN under all operating conditions.



Absolute Maximum Ratings (Notes 1, 2)

VIN, VOUT, V SHDN, VSET, VCC, V FAULT -0.3V to 6.0V Thermal Resistance (0JA) (Note 3)

Power Dissipation (Note 3) SOT-23-5 250°C/W Storage Temperature Range -65°C to160°C SOT-23-6 250°C/W

Junction Temperature (TJ) 150°C

Lead Temperature (10 sec.) 260°C

ESD Rating Operating Ratings (Note 1), (Note 2)

Human Body Model (Note 5) 2kV Temperature Range -40°C to 85°C MM 200V Supply Voltage 2.5V to 5.5V

Electrical Characteristics

Unless otherwise specified, all limits guaranteed for $V_{IN} = V_{OUT} + 1V$ (Note 6), $V | SHDN | = V_{IN}$, $C_{IN} = C_{OUT} = 2.2 \mu F$, $C_{CC} = 33 n F$, $T_{J} = 2.2 \mu F$, $C_{CC} = 33 n F$, $T_{J} = 2.2 \mu F$, $C_{CC} = 33 n F$, $T_{J} = 2.2 \mu F$, $C_{CC} = 33 n F$, $T_{J} = 2.2 \mu F$, $C_{CC} = 33 n F$, $T_{J} = 2.2 \mu F$, $C_{CC} = 33 n F$, $T_{J} = 2.2 \mu F$, $C_{CC} = 33 n F$, $T_{J} = 2.2 \mu F$, $C_{CC} = 33 n F$, $T_{J} = 2.2 \mu F$, $C_{CC} = 33 n F$, $T_{J} = 2.2 \mu F$, $C_{CC} = 33 n F$, $T_{J} = 2.2 \mu F$, $C_{CC} = 33 n F$, $T_{J} = 2.2 \mu F$, $C_{CC} = 33 n F$, $T_{J} = 2.2 \mu F$, $C_{CC} = 33 n F$, $T_{J} = 2.2 \mu F$, $T_{CC} = 33 n F$, $T_{J} = 2.2 \mu F$, $T_{CC} = 33 n F$, $T_{J} = 2.2 \mu F$, $T_{CC} = 33 n F$, $T_{$

25°C. **Boldface** limits apply for the operating temperature extremes: -40°C and 85°C.

Symbol	Parameter	Conditions	Min	Typ (Note 7)	Max	Units	
V_{IN}	Input Voltage		2.5		5.5	V	
		$100\mu A \le I_{OUT} \le 300mA$ $V_{OUT\ (NOM)} +0.5V \le VIN \le 5.5V$	-2		+2	- % of	
ΔV_{OTL}	Output Voltage Tolerance	(Note 6) ADJ = VOUT for the Adjust Versions	-3		+3	V _{OUT} (NOM)	
V_{OUT}	Output Adjust Range		1.20		5.0	V	
l _{out}	Maximum Output Current	Average DC Current Rating	600			mA	
I _{LIMIT}	Output Current Limit (SOT-23-5, SOT-23-6)		600	950		mA	
	Commands Commands	I _{OUT} = 0mA	110				
lQ	Supply Current	I _{OUT} = 600mA		255		μΑ	
	Shutdown Supply Current	$V_{OUT} = 0V$, $\overline{SHDN} = GND$		0.001	1		
	D 11/1	I _{OUT} = 50mA		22		mV	
V_{DO}	Dropout Voltage	I _{OUT} = 300mA		130			
	(Note 4), (Note 6)	I _{OUT} = 600mA		270			
ΔV_OUT	Line Regulation	$I_{OUT} = 1 \text{mA}, (V_{OUT} + 0.5 \text{V}) \le V_{IN}$ $\le 5.5 \text{V}$ (Note 7)	-0.1	0.02	0.1	%/V	
	Load Regulation	100µA ≤ I _{OUT} ≤ 600mA		0.001		%/mA	
en	Output Voltage Noise	$I_{OUT} = 10 \text{mA}, 10 \text{Hz} \le f \le 100 \text{kHz}$		30		μV _{RMS}	
. _		V_{IH} , $(V_{OUT} + 0.5V) \le V_{IN} \le 5.5V$ (Note 6)	1.2			V	
V SHDN	SHDN Input Threshold	V_{IL} , $(V_{OUT} + 0.5V) \le V_{IN} \le 5.5V$ (Note 6)			0.4		
I SHDN	SHDN Input Bias Current	SHDN = GND or VIN		0.1	100	nA	
I _{ADJ}	ADJ Input Leakage	ADJ=1.3V,		0.1	3	nA	
T _{SD}	Thermal Shutdown Temperature			165		$^{\circ}$	

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	Thermal Shutdown Hysteresis		30	
T _{ON}	Start-Up Time	Cout = 10µF, Vout at 90% of Final Value	80	μs

- **Note 1:** Absolute Maximum ratings indicate limits beyond which damage may occur. Electrical specifications do not apply when operating the device outside of its rated operating conditions.
- Note 2: All voltages are with respect to the potential at the ground pin.
- Note 3: Maximum Power dissipation for the device is calculated using the following equations:

$$P_D = \frac{T_J(MAX)^{-T}A}{\theta_{JA}}$$

where TJ(MAX) is the maximum junction temperature, TA is the ambient temperature, and $\theta_{\rm JA}$ is the junction-to-ambient thermal resistance. E.g. for the MSOP-8 package $\theta_{\rm JA}$ = 223°C/W, T_J (MAX) = 150°C and using TA = 25°C, the maximum power dissipation is found to be 561mW. The derating factor (-1/ $\theta_{\rm JA}$) = -4.5mW/°C, thus below 25°C the power dissipation figure can be increased by 4.5mW per degree, and similarity decreased by this factor for temperatures above 25°C.

- Note 4: Typical Values represent the most likely parametric norm.
- Note 5: Human body model: $1.5k\Omega$ in series with 100pF.
- Note 6: Condition does not apply to input voltages below 2.5V since this is the minimum input operating voltage.
- Note 7: Dropout voltage is measured by reducing V_{IN} until V_{OUT} drops 100mV from its nominal value at V_{IN} - V_{OUT} = 0.5V. Dropout voltage does not apply to the regulator versions with V_{OUT} less than 2.5V.

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Functional Block Diagram

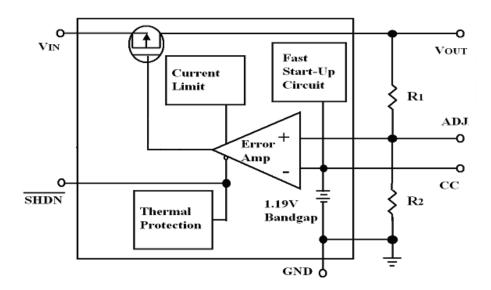
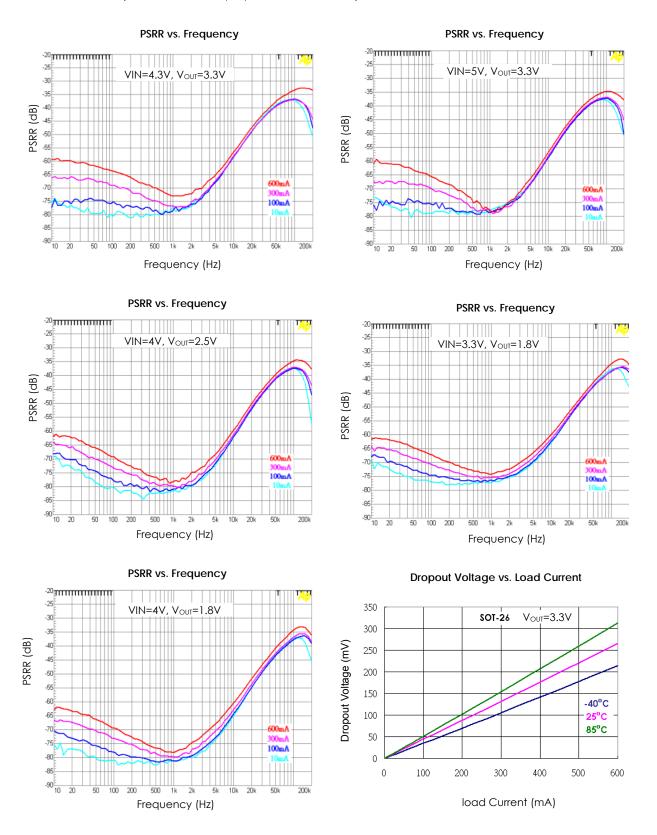


Fig.2. The EMP8966 Functional Block Diagram



Typical Performance Characteristics

Unless otherwise specified, VIN = $V_{OUT (NOM)}$ + 1V, C_{IN} = C_{OUT} = 2.2 μ F, C_{CC} = 33nF, T_A = 25°C, $V_{\overline{SHDN}}$ = VIN.

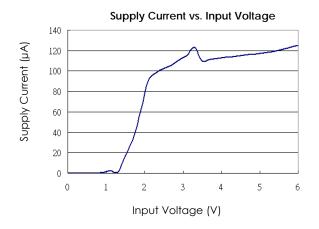


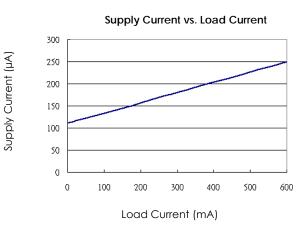
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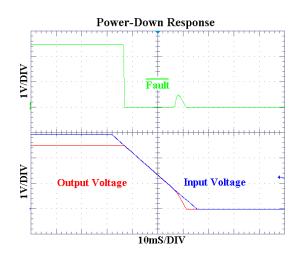


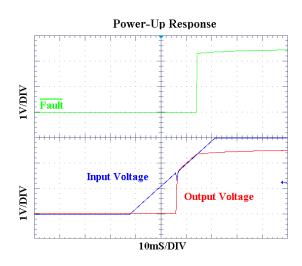
Typical Performance Characteristics

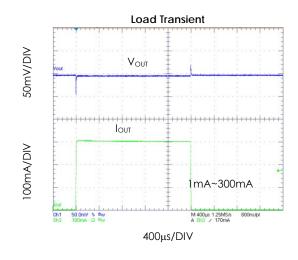
Unless otherwise specified, VIN = $V_{OUT (NOM)} + 1V$, $C_{IN} = C_{OUT} = 2.2 \mu F$, $C_{CC} = 33 n F$, $T_A = 25 ^{\circ}C$, $V_{SHDN} = VIN$. (Continued)

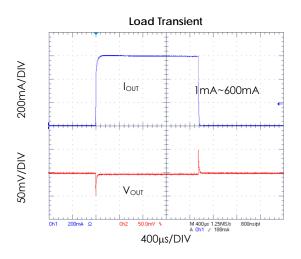










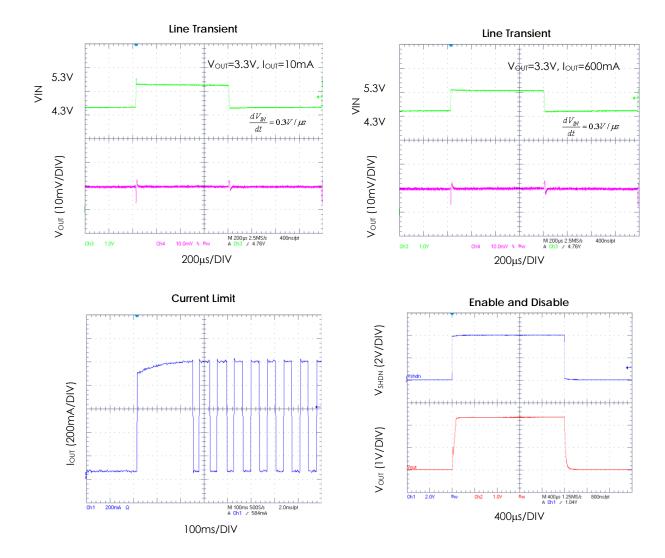


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Typical Performance Characteristics

Unless otherwise specified, VIN = $V_{OUT\ (NOM)}$ + 1V, C_{IN} = C_{OUT} = 2.2 μ F, C_{CC} = 33nF, T_A = 25°C, V_{SHDN} = VIN. (Continued)



Application Information

General Description

Referring to Figure 2 as shown in the Functional Block Diagram section, the EMP8966 adopts the classical regulator topology in which negative feedback control is used to perform the desired voltage regulating function. The negative feedback is formed by using feedback resistors (R1, R2) to sample the output voltage for the non-inverting input of the error amplifier, whose inverting input is set to the bandgap reference voltage. By virtue of its high open-loop gain, the error amplifier operates to ensure that the sampled output feedback voltage at its non-inverting input is virtually equal to the preset bandgap reference voltage. These feedback resistors can be either internal or external to the EMP8966, depending on whether a preset or an adjustable output voltage version is being used.

The error amplifier compares the voltage difference at its inputs and produces an appropriate driving voltage to the P-channel MOS pass transistor to control the amount of current reaching the output. If there are changes in the output voltage due to load changes, the feedback resistors register such changes to the non-inverting input of the error amplifier. The error amplifier then adjusts its driving voltage to maintain virtual short between its two input nodes under all loading conditions. In a nutshell, the regulation of the output voltage is achieved as a direct result of the error amplifier keeping its input voltages equal. This negative feedback control topology is further augmented by the shutdown, the fault detection, and the temperature and current protection circuitry.

Output Voltage Control

The EMP8966 allows direct user control of the output voltage in accordance with the amount of negative feedback present. To see the explicit relationship between the output voltage and the negative feedback, it is convenient to conceptualize the EMP8966 as an ideal non-inverting operational amplifier with a fixed DC reference voltage VREF at its non-inverting input. Such a conceptual representation

of the EMP8966 in closed-loop configuration is shown in

Figure 3. This ideal op amp features an ultra-high input resistance such that its inverting input voltage is virtually fixed at VREF. The output voltage is therefore given by:

$$V_{OUT} = V_{REF} \left[\frac{R_1}{R_2} + 1 \right]$$

This equation can be rewritten in the following form to facilitate the determination of the resistor values for a chosen output voltage:

$$R_1 = R_2 \left[\frac{V_{OUT}}{1.19V} - 1 \right]$$

Set R2 equal to $100k\Omega$ to optimize for overall accuracy, power supply rejection, noise, and power consumption.

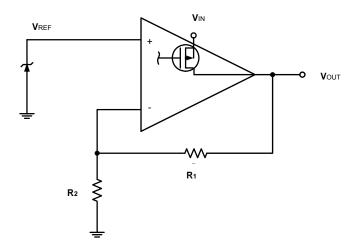


Figure 3. Simplified Regulator Topology

Output Capacitor

The EMP8966 is specially designed for use with ceramic output capacitors of as low as 2.2µF to take advantage of the savings in cost and space as well as the superior filtering of high frequency noise. Capacitors of higher value or other types may be used, but it is important to make sure its equivalent series resistance (ESR) be restricted to less than 0.5Ω . The use of larger capacitors with smaller ESR values is desirable for applications involving large and fast input or output transients, as well as for situations where the application systems are not physically located immediately adjacent to the

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Application Information (Continued)

battery power source. Typical ceramic capacitors suitable for use with the EMP8966 are X5R and X7R. The X5R and the X7R capacitors are able to maintain their capacitance values to within $\pm 20\%$ and $\pm 10\%$, respectively, as the temperature increases.

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No-Load Stability

The EMP8966 is capable of stable operation during no-load conditions, a mandatory feature for some applications such as CMOS RAM keep-alive operations.

Input Capacitor

A minimum input capacitance of 1µF is required for EMP8966. The capacitor value may be increased without limit. Improper workbench set-ups may have adverse effects on the normal operation of the regulator. A case in point is the instability that may result from long supply lead inductance coupling to the output through the gate capacitance of the pass transistor. This will establish a pseudo LCR network, and is likely to happen under high current conditions or near dropout. A 10µF tantalum input capacitor will dampen the parasitic LCR action thanks to its high ESR. However, cautions should be exercised to avoid regulator short-circuit damage when tantalum capacitors are used, for they are prone to fail in short-circuit operating conditions.

Compensation (Noise Bypass) Capacitor

Substantial reduction in the output voltage noise of the EMP8966 is accomplished through the connection of the noise bypass capacitor CC (33nF optimum) between pin 4(sot-23-6) and the ground. Because pin 4(sot-23-6) connects directly to the high impedance output of the bandgap reference circuit, the level of the DC leakage currents in the CC capacitors used will adversely reduce the regulator output voltage. This sets

the DC leakage level as the key selection criterion of the CC capacitor types for use with the EMP8966. NPO and COG ceramic capacitors typically offer very low leakage. Although the use of the CC capacitors does not affect the transient response, it does affect the turn-on time of the regulator. Tradeoff exists between output noise level and turn-on time when selecting the CC capacitor value.

Power Dissipation and Thermal Shutdown

Thermal overload results from excessive power dissipation that causes the IC junction temperature to increase beyond a safe operating level. The EMP8966 relies on dedicated thermal shutdown circuitry to limit its total power dissipation. An IC junction temperature TJ exceeding 165°C will trigger the thermal shutdown logic, turning off the P-channel MOS pass transistor. The pass transistor turns on again after the junction cools off by about 30°C. When continuous thermal overload conditions persist, this thermal shutdown action then results in a pulsed waveform at the output of the regulator. The concept of thermal resistance θ_{JA} (°C/W) is often used to describe an IC junction's relative readiness in allowing its thermal energy to dissipate to its ambient air. An IC junction with a low thermal resistance is preferred because it is relatively effective in dissipating its thermal energy to its ambient, thus resulting in a relatively low and desirable junction temperature. The relationship between $\, heta$ JA $\,$ and TJ is as follows:

$$T_J = \theta_{JA}$$
 (PD) + T_A

 T_{A} is the ambient temperature, and P_{D} is the power generated by the IC and can be written as:

$$P_D = I_{OUT} (V_{IN} - V_{OUT})$$

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As the above equations show, it is desirable to work with ICs whose θ_{JA} values are small such that T_J does not increase strongly with P_D . To avoid thermally overloading the EMP8966, refrain from exceeding the absolute maximum junction temperature rating of

Application Information (Continued)

150°C under continuous operating conditions. Overstressing the regulator with high loading currents and elevated input-to-output differential voltages can increase the IC die temperature significantly. **Shutdown**

The EMP8966 enters the sleep mode when the SHDN pin is low. When this occurs, the pass transistor, the error amplifier, and the biasing circuits, including the bandgap reference, are turned off, thus reducing the supply current to typically 1nA. Such a low supply current makes the EMP8966 best suited for battery-powered applications. The

maximum guaranteed voltage at the SHDN pin for the sleep mode to take effect is 0.4V. A minimum guaranteed

voltage of 1.2V at the \overline{SHDN} pin will activate the EMP8966. Direct connection of the \overline{SHDN} pin to the VIN to keep the regulator on is allowed for the EMP8966. In this case, the \overline{SHDN} pin must not exceed the supply voltage VIN.

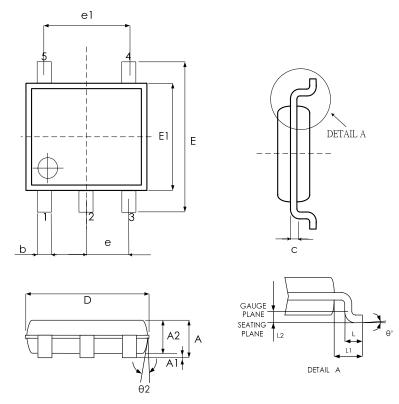
Fast Start-Up

Fast start-up time is important for overall system efficiency improvement. The EMP8966 assures fast start-up speed when using the optional noise bypass capacitor (CC). To shorten start-up time, the EMP8966 internally supplies a 500 μ A current to charge up the capacitor until it reaches a b o u t 90% o f i t s f i n a l v a l u e .

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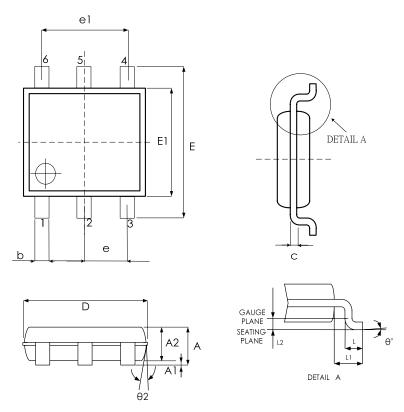
Physical Dimensions SOT-23-5



SYMBPLS	MIN.	NOM.	MAX.		
Α	1.05	1.20	1.35		
A1	0.05	0.10	0.15		
A2	1.00	1.10	1.20		
b	0.30	_	0.50		
С	0.08	_	0.20		
D	2.80	2.90	3.00		
Е	2.60	2.80	3.00		
E1	1.50	1.60	1.70		
е	0.95 BSC				
e1		1.90 BSC			
L	0.30	0.45	0.55		
L1		0.60 REF			
θ°	θ° 0		10		
θ2°	6	8	10		

UNIT: MM

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SYMBPLS	MIN.	NOM.	MAX.			
Α	_	_	1.45			
A1	_	_	0.15			
A2	0.90	1.15	1.30			
b	0.30	_	0.50			
С	0.08	_	0.22			
D	2.90 BSC.					
Е	2.80 BSC.					
E1	1.60 BSC.					
е	0.95 BSC					
el	1.90 BSC					
L	0.30	0.45	0.60			
L1	0.60 REF					
L2	0.25 REF					
θ°	0	4	8			
θ2°	5	10	15			

UNIT: MM



Notice

Order, Mark & Packing Information

No. of PIN	Adj	EN	СС	Vout	Package	Old Marking		Product ID	
5	5 Y Y N Adi SOT-23-5		P630	P630 Date Code	EMP8966-00VF05GRR				
						Trac	8965 king Code		
6	Y	Υ	Y	Adj	SOT-23-6	P630	P630 Date Code	EMP8966-00VC06GRR	

Package & Packing

SOT-23-5	3K units Tape & Reel
SOT-23-6	3K units Tape & Reel

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Revision History

Revision	Date	Description
1.0	2008.10.07	Original
1.1	2009.05.08	Modify order information
1.2	2014.12.29	Remove SOT-89-5

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